IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application

Applicant(s): Allen et al.
Docket No.: YOR920030175US1
Serial No.: 10/661,041
Filed: September 12, 2003
Group: 2811
Examiner: Unassigned

I hereby certify that this paper is being deposited on this date with the U.S. Postal Service as first class mail addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

Signature: _____ Date: January 21, 2004

Title: Techniques for Patterning Features in Semiconductor Devices

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INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying PTO Form 1449.

U.S. Patent

1. U.S. Patent No. 6,316,167

Copies of each of the following listed items are enclosed:

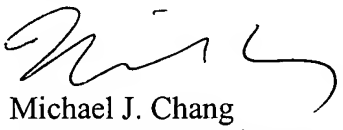
Other Documents

2. Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
3. Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).
4. DellaGuardia et al., "193 Lithography and RELACS™ Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).
5. Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
6. Satou et al., "Sub-0.10 μm Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or the credit **International Business Machines Corporation's Deposit Account No. 50-0510** as required to correct the error.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability or as a representation that no other material information exists.

Respectfully submitted,



Date: January 21, 2004

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FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
_____	6,316,167	11/13/01	Angelopoulos et al.	430/313	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	TRANSLATION YES	NO
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OTHER DOCUMENTS

EXAMINER INITIAL	REF NO.	AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.
_____		Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
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_____		Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
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Examiner _____ Date Considered _____

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.